

< C band internally matched power GaAs FET >

MGFC39V7177A

7.1 – 7.7 GHz BAND / 8W

DESCRIPTION

The MGFC39V7177A is an internally impedance-matched GaAs power FET especially designed for use in 7.1 – 7.7 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class A operation

Internally matched to 50(ohm) system

- High output power
P1dB=8W (TYP.) @f=7.1 – 7.7GHz
- High power gain
GLP= 8.0dB (TYP.) @f=7.1 – 7.7GHz
- High power added efficiency
P.A.E.=28% (TYP.) @f=7.1 – 7.7GHz
- Low distortion [item -51]
IM3=-45dBc (TYP.) @Po=28dBm S.C.L

APPLICATION

- item 01 : 7.1 – 7.7 GHz band power amplifier
- item 51 : 7.1 – 7.7 GHz band digital radio communication

QUALITY

- IG

RECOMMENDED BIAS CONDITIONS

- VDS=10V • ID=2.4A Refer to Bias Procedure • RG=50ohm

Absolute maximum ratings (Ta=25°C)

Symbol	Parameter	Ratings	Unit
VGDO	Gate to drain breakdown voltage	-15	V
VGSO	Gate to source breakdown voltage	-15	V
ID	Drain current	7.5	A
IGR	Reverse gate current	-20	mA
IGF	Forward gate current	42	mA
PT *1	Total power dissipation	42.8	W
Tch	Cannel temperature	175	°C
Tstg	Storage temperature	-65 to +175	°C

*1 : Tc=25°C

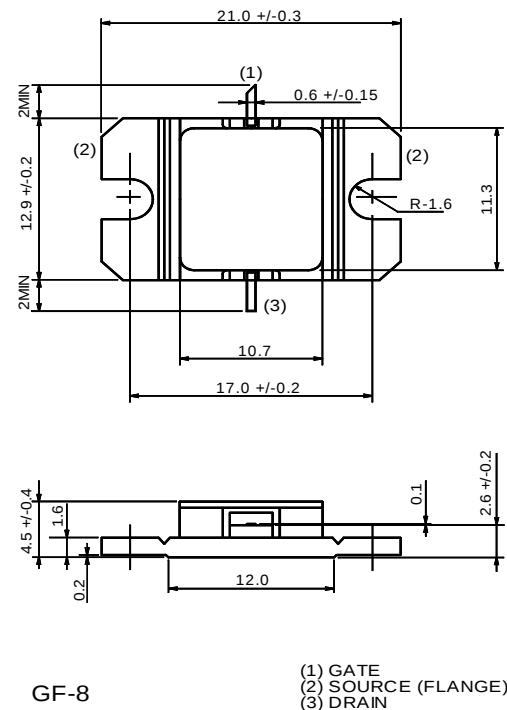
Electrical characteristics (Ta=25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
IDSS	Saturated drain current	VDS=3V,VGS=0V	-	-	7.5	A
gm	Transconductance	VDS=3V,ID=2.2A	-	2	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V,ID=20mA	-	-	-4.5	V
P1dB	Output power at 1dB gain compression	VDS=10V,ID(RF off)=2.4A f=7.1 – 7.7GHz	38	39.5	-	dBm
GLP	Linear Power Gain		7	8	-	dB
ID	Drain current		-	-	3	A
P.A.E.	Power added efficiency		-	28	-	%
IM3 *2	3rd order IM distortion		-42	-45	-	dBc
Rth(ch-c) *3	Thermal resistance	delta Vf method	-	-	3.5	°C/W

*2 : item -51 ,2 tone test,Po=28dBm Single Carrier Level ,f=7.7GHz,delta f=10MHz

*3 :Channel-case

OUTLINE DRAWING Unit : millimeters



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